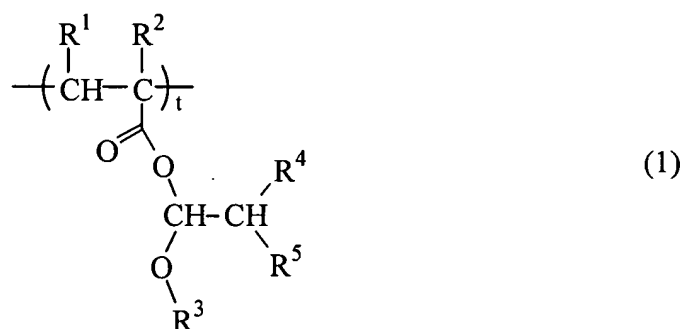
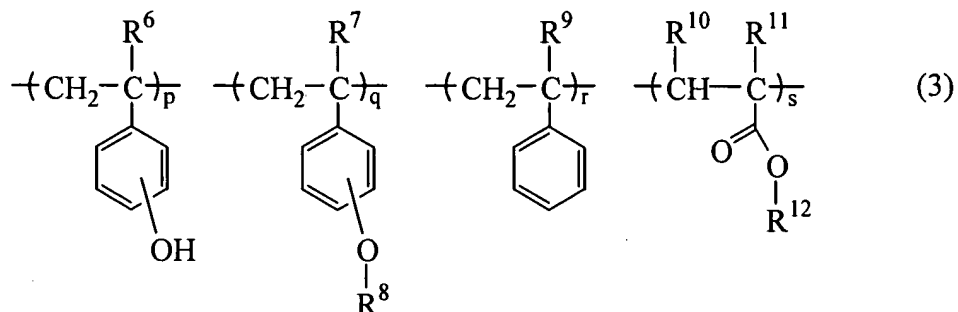


AMENDMENTS TO THE CLAIMS

1. (Cancelled)
2. (Cancelled)
3. (Original) A resist composition comprising a polymer comprising recurring units of the following general formula (1) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000,

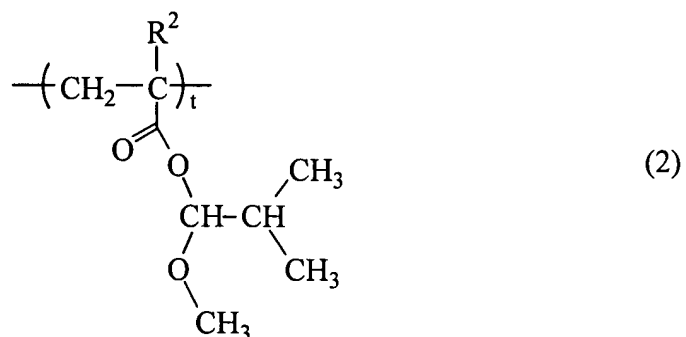


wherein  $\text{R}^1$  and  $\text{R}^2$  are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group,  $\text{R}^3$  is methyl or ethyl,  $\text{R}^4$  and  $\text{R}^5$  each are an alkyl group having 1 to 7 carbon atoms, or  $\text{R}^4$  and  $\text{R}^5$  may bond together to form a cyclic structure,  $t$  is a positive number,

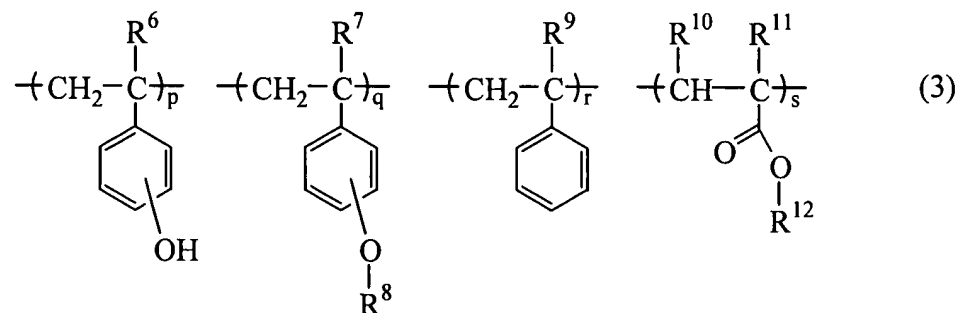


wherein  $\text{R}^6$ ,  $\text{R}^7$ ,  $\text{R}^9$ ,  $\text{R}^{10}$  and  $\text{R}^{11}$  are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group,  $\text{R}^8$  is an alkyl group having 1 to 10 carbon atoms,  $\text{R}^{12}$  is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group,  $q$ ,  $r$  and  $s$  are 0 or positive numbers, and  $p$  is a positive number.

4. (Original) A resist composition comprising a polymer comprising recurring units of the following general formula (2) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000,



wherein  $R^2$  is hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, and  $t$  is a positive number,



wherein  $R^6$ ,  $R^7$ ,  $R^9$ ,  $R^{10}$  and  $R^{11}$  are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group,  $R^8$  is an alkyl group having 1 to 10 carbon atoms,  $R^{12}$  is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group,  $q$ ,  $r$  and  $s$  are 0 or positive numbers, and  $p$  is a positive number.

5. (Currently Amended) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 1 3 as a base resin, and
- (C) a photoacid generator.

6. (Currently Amended) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim ~~4~~ 3 as a base resin,
- (C) a photoacid generator, and
- (D) a dissolution inhibitor.

7. (Original) The chemically amplified positive resist composition of claim 5, further comprising (E) a basic compound.

8. (Currently Amended) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim ~~4~~ 3 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

9. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 4 as a base resin, and
- (C) a photoacid generator.

10. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 4 as a base resin,
- (C) a photoacid generator, and
- (D) a dissolution inhibitor.

11. (New) The chemically amplified positive resist composition of claim 9, further comprising (E) a basic compound.

12. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 9 onto a substrate to form a coating,

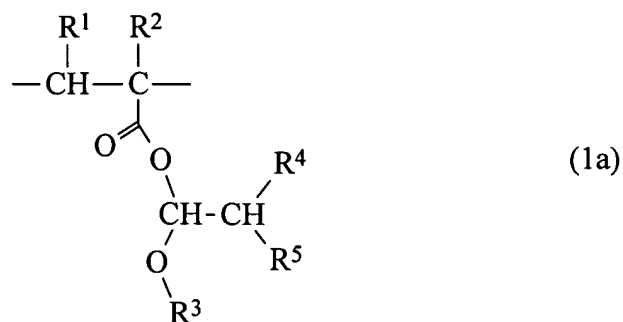
heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

13. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,

(B) a polymer as a base resin comprising recurring units of the following general formula (1a) and having a weight average molecular weight of 1,000 to 500,000,



wherein  $\text{R}^1$  and  $\text{R}^2$  are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group,  $\text{R}^3$  is methyl or ethyl,  $\text{R}^4$  and  $\text{R}^5$  each are an alkyl group having 1 to 7 carbon atoms, or  $\text{R}^4$  and  $\text{R}^5$  may bond together to form a cyclic structure,

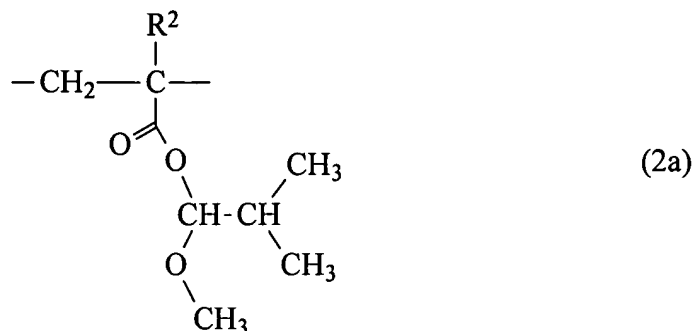
(C) a photoacid generator, and

(D) a basic compound.

14. (New) A chemically amplified positive resist composition comprising

(A) an organic solvent,

(B) a polymer as a base resin comprising recurring units of the following general formula (2a) and having a weight average molecular weight of 1,000 to 500,000,



wherein  $\text{R}^2$  is a hydrogen, hydroxyl, a straight or branched alkyl group, halogen atom or trifluoromethyl group,

(C) a photoacid generator, and

(D) a basic compound.

15. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 13 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

16. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 14 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.